INFORMATION DISCLOSURE CITATION		ATTY. DOCKET NO.			SERIA	SERIAL NO.				
		925-327			10/53	10/552,268				
		APPLICANT				,				
			ASANO ET AL.							
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Xie et al, "A High-Current and High-Temperature 6H-SiC Thyristor", IEEE Electron Device Letters, vol. 17, no. 3, March 1996, pp. 142-144										
<u> </u>	1			Date Consider	ed					
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